BAW56L, SBAW56L

Dual Switching Diode Common Anode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	70	V
Forward Current	١ _F	200	mA
Forward Surge Current (60 Hz @ 1 cycle)	I _{FSM}	2.0	A
Non–Repetitive Peak Forward Current t = 1 μ s (Note 3)	I _{FSM}	4.0	A
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I _{FRM}	500	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

3. Square Wave; $T_i = 25^{\circ}C$.

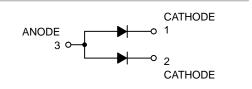


ON Semiconductor®

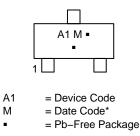
www.onsemi.com







MARKING DIAGRAM



(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BAW56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SBAW56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BAW56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SBAW56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

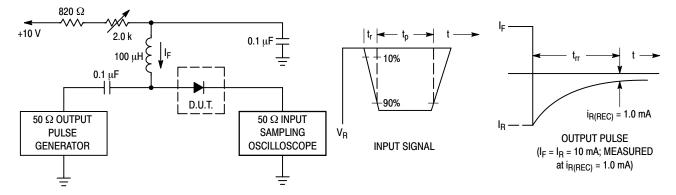
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAW56L, SBAW56L

ELECTRICAL	CHARACTERISTICS (T _A =	= 25°C unless otherwise noted)	(Each Diode)
------------	-----------------------------------	--------------------------------	--------------

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage $(I_{(BR)} = 100 \ \mu A)$	V _(BR)	70	_	V
Reverse Voltage Leakage Current $(V_R = 25 \text{ V}, \text{ T}_J = 150^{\circ}\text{C})$ $(V_R = 70 \text{ V})$ $(V_R = 70 \text{ V}, \text{ T}_J = 150^{\circ}\text{C})$	I _R	- - -	30 2.5 50	μΑ
Diode Capacitance (V _R = 0 V, f = 1.0 MHz)	C _D	_	2.0	pF
Forward Voltage $(I_F = 1.0 \text{ mA})$ $(I_F = 10 \text{ mA})$ $(I_F = 50 \text{ mA})$ $(I_F = 150 \text{ mA})$	V _F	- - -	715 855 1000 1250	mV
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}, I_{R(REC)} = 1.0 \text{ mA}$) (Figure 1) $R_L = 100 \Omega$	t _{rr}	_	6.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA. 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA. 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BAW56L, SBAW56L

Curves Applicable to Each Cathode

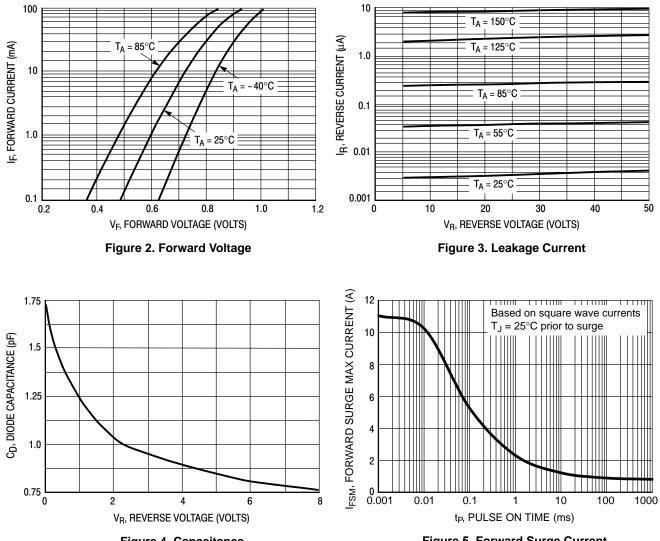


Figure 4. Capacitance

Figure 5. Forward Surge Current

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

onsemi



SCALE 4:1

A____ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-L1

DETAIL A

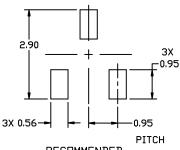
END VIEW

DATE 01 MAR 2023

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η _E	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	N: SOT-23 (TO-236)		PAGE 1 OF 2	
the right to make changes without furth purpose, nor does onsemi assume a	er notice to any products herein. onsemi make ny liability arising out of the application or use	LLC dba onsemi or its subsidiaries in the United States and/or other cours s no warranty, representation or guarantee regarding the suitability of its pr of any product or circuit, and specifically disclaims any and all liability, inc e under its patent rights nor the rights of others.	roducts for any particular	

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

onsemi

SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2	

onsemi and ONSEMi. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales